

In the Claims:

Please amend the following claims:

(C1)
B'

1. (Amended) A method of forming a dielectric layer in an opening, comprising:
forming a first dielectric layer in the opening at a first deposition rate, the opening having an aspect ratio greater than about two, and wherein a portion of the opening not filled with said first dielectric layer has an aspect ratio of not greater than about two; and
forming a second dielectric layer over the first dielectric layer at a second deposition rate greater than said first deposition rate, the second layer having a top surface that is not within the opening.

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14. (Amended) A method of forming a dielectric layer during the manufacture of a semiconductor device, comprising:
providing a substrate;
forming an opening relative to the substrate, the opening having an aspect ratio greater than about two;
forming a first dielectric layer in the opening at a first deposition rate, wherein a portion of the opening not filled with said first dielectric layer has an aspect ratio of not greater than about two; and
forming a second dielectric layer over the first dielectric layer at a second deposition rate greater than said first deposition rate, the second layer having a top surface that is not within the opening.

19. (Amended) A method of forming a dielectric layer in an opening, comprising:

forming a first dielectric layer in the opening at a first deposition rate, the first layer having a first process setting; and

B³ forming a second dielectric layer over the first dielectric layer at a second deposition rate greater than said first deposition rate, the second layer having a top surface that is not within the opening and having a second process setting at a predetermined relationship with the first process setting.

26. (Amended) A method of forming a dielectric layer in an opening, comprising:

forming a first dielectric layer completely filling the opening at a first deposition rate, the opening having an aspect ratio greater than about two; and

B⁴ forming a second dielectric layer over the first dielectric layer at a second deposition rate greater than said first deposition rate.

27. (Amended) A method of forming a dielectric layer in an opening, comprising:

forming a first dielectric layer in the opening at a first deposition rate, the first layer being formed at a first temperature; and

forming a second dielectric layer over the first dielectric layer at a second deposition rate greater than said first deposition rate, the second layer having a top surface that is not within the opening and being formed at a second temperature, the first temperature being greater than the second temperature.

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cont'd

28. (Amended) A method of forming a dielectric layer in an opening, comprising:
forming a first dielectric layer in the opening at a first deposition rate, the first layer being formed at a first pressure; and
forming a second dielectric layer over the first dielectric layer at a second deposition rate greater than said first deposition rate, the second layer having a top surface that is not within the opening and being formed at a second pressure, the first pressure being greater than the second pressure.

29. (Amended) A method of forming a dielectric layer in an opening, comprising:
forming a first dielectric layer in the opening at a first deposition rate, the first layer having a first dopant concentration; and
forming a second dielectric layer over the first dielectric layer at a second deposition rate greater than said first deposition rate, the second layer having a top surface that is not within the opening and having a second dopant concentration, the first dopant concentration being less than the second dopant concentration.

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31. (Amended) A method of forming a dielectric layer in an opening, comprising:
forming a first dielectric layer in the opening at a first deposition rate, said forming the first layer including:
providing a shower head at a first distance from the substrate, and
providing through the shower head constituents forming the first layer; and